IRFPC50

Vishay Siliconix



TO-247AC

PRODUCT SUMMARY

V_{DS} (V)

R_{DS(on)} (Ω)

Q_g (max.) (nC)

Q_{gs} (nC)

Q_{ad} (nC)

Configuration

Power MOSFET

S

N-Channel MOSFET

0.60

600

140

20

69

Single

V_{GS} = 10 V

FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- Isolated central mounting hole
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-247AC package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220AB devices. The TO-247AC is similar but superior to the earlier TO-218 package because of its isolated mounting hole. It also provides greater creepage distance between pins to meet the requirements of most safety specifications.

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-free	IRFPC50PbF

ABSOLUTE MAXIMUM RATINGS (T _C	= 25 °C, unl	ess otherwis	se noted)		
PARAMETER	PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage			V _{DS}	600	V
Gate-source voltage		V _{GS}	± 20	v	
Continuous drain current	V _{GS} at 10 V	$T_C = 25 \ ^\circ C$		11	
Continuous drain current	VGS AL TO V	T _C = 100 °C	Ι _D	7.0	А
Pulsed drain current ^a		I _{DM}	44		
Linear derating factor			1.4	W/°C	
Single pulse avalanche energy ^b		E _{AS}	920	mJ	
Repetitive avalanche current ^a	Repetitive avalanche current ^a		I _{AR}	10	А
Repetitive avalanche energy ^a			E _{AR}	18	mJ
Maximum power dissipation	T _C = 25 °C		PD	180	W
Peak diode recovery dV/dt ^c			dV/dt	3.0	V/ns
Operating junction and storage temperature range			T _J , T _{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) for 10 s				300 ^d	
Mounting torque	6.32 or M2	CON		10	lbf · in
Mounting torque	0-32 OF 1013 S	6-32 or M3 screw		1.1	N · m

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

b. $V_{DD} = 50$ V, starting $T_J = 25$ °C, L = 13 mH, $R_g = 25 \Omega$, $I_{AS} = 11$ A (see fig. 12)

c. $I_{SD} \le 11$ A, dI/dt ≤ 100 A/µs, $V_{DD} \le V_{DS}$, $T_J \le 150$ °C

d. 1.6 mm from case

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THERMAL RESISTANCE					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R _{thJA}	-	-	40	
Case-to-sink, flat, greased surface	R _{thCS}	-	0.24	-	°C/W
Maximum junction-to-case (drain)	R _{thJC}	-	-	0.65	

PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						•	
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 V, I_D =$	= 250 μA	600	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	Reference to	25 °C, I _D = 1 mA	-	0.78	-	V/°C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D$	= 250 μA	2.0	-	4.0	V
Gate-source leakage	I _{GSS}	$V_{GS} = \pm 20 V$		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 600 V, V		-	-	100	μA
			V _{GS} = 0 V, T _J = 125 °C	-	-	500	r
Drain-source on-state resistance	R _{DS(on)}	$V_{GS} = 10 V$		-	-	0.60	Ω
Forward transconductance	9 _{fs}	V _{DS} = 100 V,	_D = 6.0 A ^b	5.7	-	-	S
Dynamic							
Input capacitance	C _{iss}	$V_{GS} = 0 V$,		-	2700	-	
Output capacitance	C _{oss}	$V_{DS} = 25 V$,	a –	-	300	-	pF
Reverse transfer capacitance	C _{rss}	f = 1.0 MHz, s	see fig. 5	-	61	-	
Output capacitance	Qg			-	-	140	
Output capacitance	Q _{gs}	$V_{GS} = 10 V$	$I_D = 11 \text{ A}, V_{DS} = 360 \text{ V}$ see fig. 6 and 13 ^b	-	-	20	nC
Effective output capacitance	Q _{gd}			-	-	69	
Total gate charge	t _{d(on)}			-	18	-	
Gate-source charge	t _r	$V_{DD} = 300 V,$	I _D = 11 A,	-	37	-	
Gate-drain charge	t _{d(off)}	$R_{g} = 6.2 \Omega, R_{f}$	$_{\rm D}$ = 30 Ω , see fig. 10 ^b	-	88	-	ns
Turn-on delay time	t _f			-	36	-	
Internal drain inductance	L _D	Between lead	·	-	5.0	-	
Internal source inductance	L _S	6 mm (0.25") package and die contact		-	13	-	nH
Drain-Source Body Diode Characteristic	s	-		•	•	•	
Continuous source-drain diode current	Is	MOSFET sym	lbol	-	-	11	
Pulsed diode forward current ^a	I _{SM}	showing the integral revers p - n junction		-	-	44	A
Body diode voltage	V _{SD}	$T_J = 25 \text{ °C}, I_S$	= 11 A, V _{GS} = 0 V ^b	-	-	1.4	V
Body diode reverse recovery time	t _{rr}	T 05 %0 1	11 A dl/dt 100 A / b	-	550	830	ns
Body diode reverse recovery charge	Q _{rr}	$I_{\rm J} = 25 {}^{-}{\rm C}, I_{\rm F}$	= 11 A, dl/dt = 100 A/µs ^b	-	3.9	5.9	μC
Forward turn-on time	t _{on}	Intrinsic turn-	on time is negligible (turn-on	is domina	ated by L	and Ln)	

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

b. Pulse width \leq 300 µs; duty cycle \leq 2 %

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

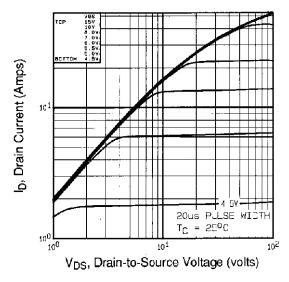


Fig. 1 - Typical Output Characteristics, $T_C = 25 \ ^\circ C$

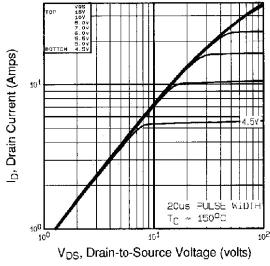


Fig. 2 - Typical Output Characteristics, T_C = 150 °C

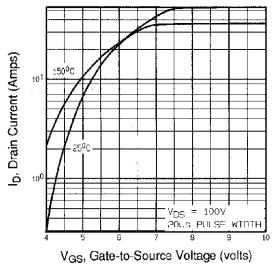


Fig. 3 - Typical Transfer Characteristics

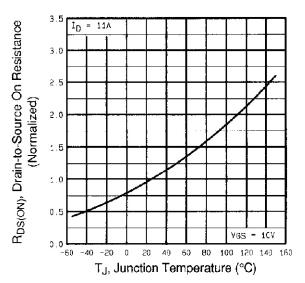


Fig. 4 - Normalized On-Resistance vs. Temperature





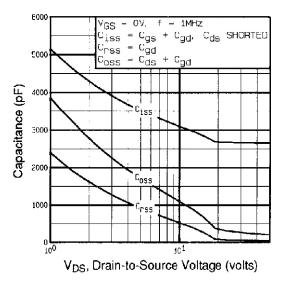


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

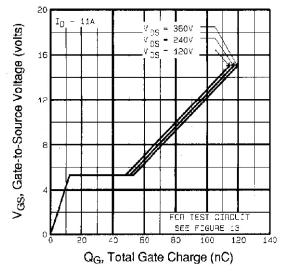


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

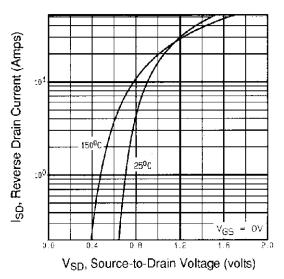


Fig. 7 - Typical Source-Drain Diode Forward Voltage

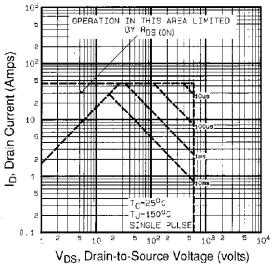


Fig. 8 - Maximum Safe Operating Area

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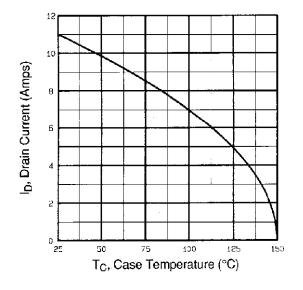


Fig. 9 - Maximum Drain Current vs. Case Temperature

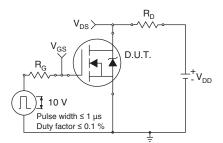


Fig. 10 - Switching Time Test Circuit

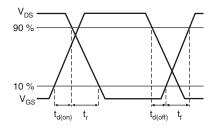


Fig. 11 - Switching Time Waveforms

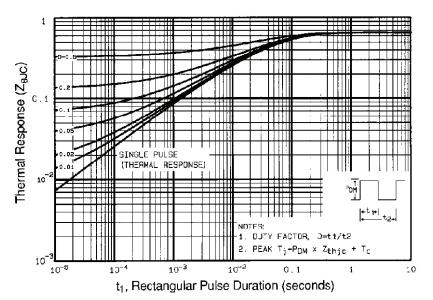


Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

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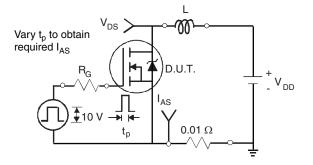


Fig. 13 - Unclamped Inductive Test Circuit

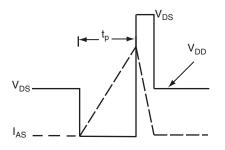


Fig. 14 - Unclamped Inductive Waveforms

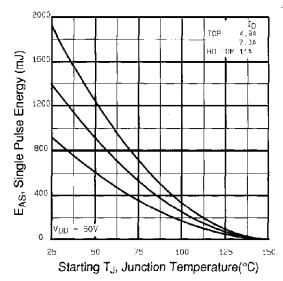


Fig. 15 - Maximum Avalanche Energy vs. Drain Current

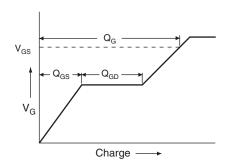


Fig. 16 - Basic Gate Charge Waveform

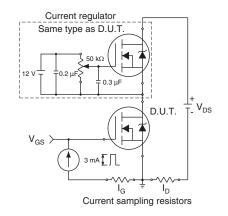


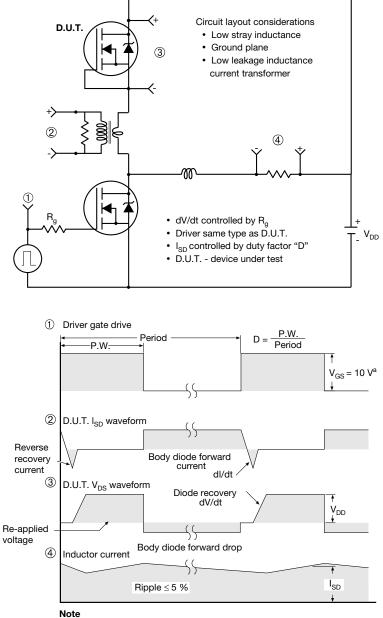
Fig. 17 - Gate Charge Test Circuit

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Peak Diode Recovery dV/dt Test Circuit



a. $V_{GS} = 5 V$ for logic level devices

Fig. 18 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91243.



TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9





Section C--C, D--D, E--E

	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
А	4.83	5.21	
A1	2.29	2.55	
A2	1.50	2.49	
b	1.12	1.33	
b1	1.12	1.28	
b2	1.91	2.39	6
b3	1.91	2.34	
b4	2.87	3.22	6, 8
b5	2.87	3.18	
С	0.55	0.69	6
c1	0.55	0.65	
D	20.40	20.70	4

	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
D1	16.25	16.85	5
D2	0.56	0.76	
E	15.50	15.87	4
E1	13.46	14.16	5
E2	4.52	5.49	3
е	5.44	BSC	
L	14.90	15.40	
L1	3.96	4.16	6
ØP	3.56	3.65	7
Ø P1	7.19) ref.	
Q	5.31	5.69	
S	5.54	5.74	

Notes

- ⁽¹⁾ Package reference: JEDEC[®] TO247, variation AC
- (2) All dimensions are in mm
- ⁽³⁾ Slot required, notch may be rounded
- ⁽⁴⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁵⁾ Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

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VERSION 2: FACILITY CODE = Y



	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
А	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
с	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	254	
L	14.20	16.25	
L1	3.71	4.29	
ØΡ	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51	BSC	

Notes

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994
- ⁽²⁾ Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁴⁾ Thermal pad contour optional with dimensions D1 and E1
- ⁽⁵⁾ Lead finish uncontrolled in L1
- ⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- ⁽⁷⁾ Outline conforms to JEDEC outline TO-247 with exception of dimension c



VERSION 3: FACILITY CODE = N



	MILLIMETERS	LIMETERS		MILLIN	IETERS
DIM.	MIN.	MAX.	DIM.	MIN.	MAX.
А	4.65	5.31	D2	0.51	1.35
A1	2.21	2.59	E	15.29	15.87
A2	1.17	1.37	E1	13.46	-
b	0.99	1.40	е	5.46	BSC
b1	0.99	1.35	k	0.:	254
b2	1.65	2.39	L	14.20	16.10
b3	1.65	2.34	L1	3.71	4.29
b4	2.59	3.43	N	7.62	BSC
b5	2.59	3.38	Р	3.56	3.66
С	0.38	0.89	P1	-	7.39
c1	0.38	0.84	Q	5.31	5.69
D	19.71	20.70	R	4.52	5.49
D1	13.08	-	S	5.51	BSC

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

⁽²⁾ Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁴⁾ Thermal pad contour optional with dimensions D1 and E1

⁽⁵⁾ Lead finish uncontrolled in L1

⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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